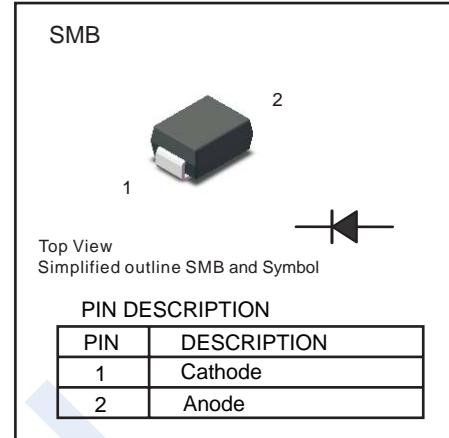


General Purpose Silicon Rectifiers

S2AB ~ S2MB

■ Features

- Reverse Voltage - 50 to 1000 V
- Forward Current - 2 A
- For surface mounted applications
- Low profile package
- Glass Passivated Chip Junction
- Easy to pick and place



■ Maximum Ratings and Electrical characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

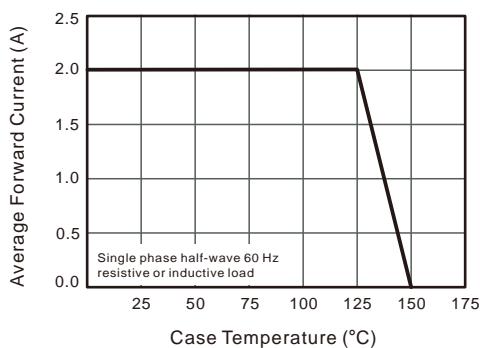
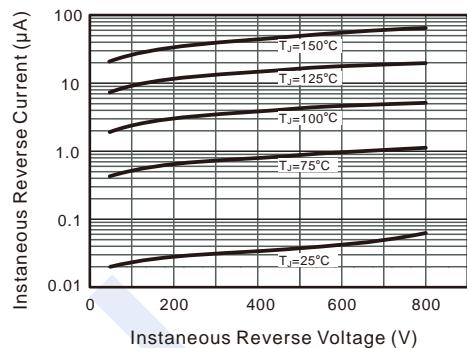
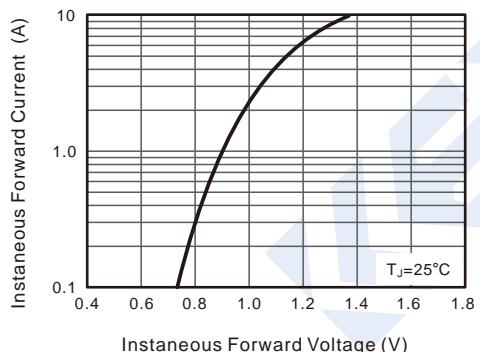
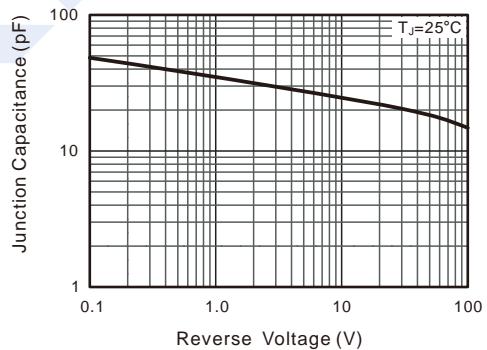
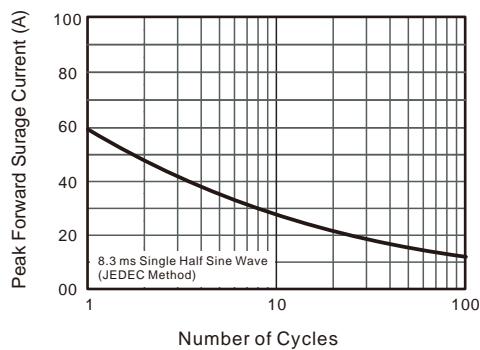
Parameter	Symbols	S2AB	S2BB	S2DB	S2GB	S2JB	S2KB	S2MB	Unit
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	
Maximum Instantaneous Forward Voltage at $I_F=2A$	V_F					1.1			
Maximum Averaged Forward Rectified Current	I_{FAV}					2			A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load	I_{FSM}					60			
Maximum DC Reverse Current $T_A=25^\circ C$ at rated DC blocking voltage $T_A=125^\circ C$	I_R				5				μA
					100				
Typical Junction Capacitance *1	C_j				25				pF
Typical Thermal Resistance *2	$R_{\theta JA}$ $R_{\theta JC}$				60				$^\circ C/W$
Junction Temperature	T_j				20				
Storage Temperature	T_{stg}				150				
					-55 to 150				$^\circ C$

* 1 Measured at 1MHz and applied reverse voltage of 4V D.C.

* 2 P.C.B. mounted with 0.2" x 0.2" (5x5mm) copper pad areas.

■ Marking

NO.	S2AB	S2BB	S2DB	S2GB	S2JB	S2KB	S2MB
Marking	S2A	S2B	S2D	S2G	S2J	S2K	S2M

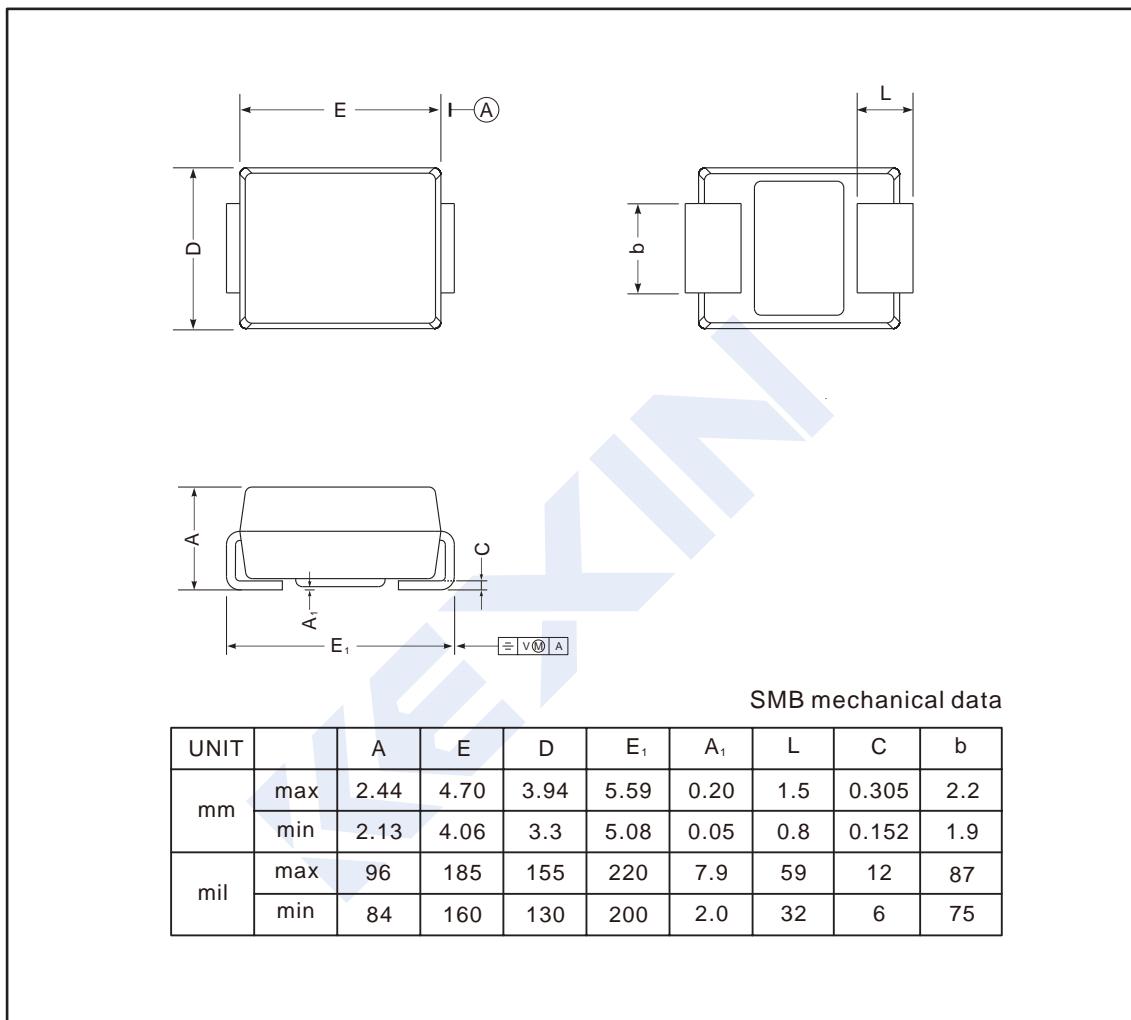
S2AB ~ S2MB**■ Typical Characteristics****Fig.1 Forward Current Derating Curve****Fig.2 Typical Instantaneous Reverse Characteristics****Fig.3 Typical Forward Characteristic****Fig.4 Typical Junction Capacitance****Fig.5 Maximum Non-Repetitive Peak Forward Surge Current**

S2AB ~ S2MB

■ Package Outline Dimensions

Plastic surface mounted package; 2 leads

SMB



■ The Recommended Mounting Pad Size

